

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1

1

of

2

Complete if Known**Application Number**

Not yet received

10/682486

Filing Date

Even date herewith

10-10-03

First Named Inventor

Pankaj B. SHAH

Group Art Unit

~~Not yet assigned~~

2813

Examiner Name

Not yet assigned

Attorney Docket Number

ARL 03-19

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

**Examiner
Signature**

Date Considered

2/15/05

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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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**INFORMATION DISCLOSURE
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Sheet 2

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
TW	AH	SOWERS, et al., "Thin films of aluminum nitride and aluminum gallium nitride for cold cathode applications," Appl. Phys. Lett., October 20, 1997, pp. 2289-2291, Vol. 71, No. 16.	
	AI	ZHELEVA, et al., "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures," Appl. Phys. Lett., October 27, 1997, pp. 2472-2474, Vol. 71, No. 17.	
	AJ	UNDERWOOD, et al., "GaN field emitter array diode with integrated anode", J. Vac. Sci. Technol. B., March/April 1998, pp. 822-825, Vol. 16, No. 2.	
	AK	KOZAWA, et al., "Field emission study of gated GaN and Al _{0.1} Ga _{0.9} N/GaN pyramidal field emitter arrays," Appl. Phys. Lett., November 22, 1999, pp. 3330-3332, Vol. 75, No. 21.	
	AL	KUBALL, et al., "Focused Ion Beam Etching of Nanometer-Size GaN/AlGaN Device Structures and Their Optical Characterization by Micro-Photoluminescence/Raman Mapping," MRS Interent J. Nitride Semicond. Res., 2000, Vol. 5S1, Art. W12.3.	
	AM	GÜNTHER, et al., "Comparison of field emission from diamond and AlN coated Si Tips," EURO FE, September 25-29, 2000, Segovia-Spain.	
	AN	KASU, et al., "Spontaneous ridge-structure formation and large field emission of heavily Si-doped AlN," Appl. Phys. Lett., March 26, 2001, pp. 1835-1837, Vol. 78, No. 13.	
	AO	SUGINO, et al., "Field emission from GaN surfaces roughened by hydrogen plasma treatment," Appl. Phys. Lett., May 21, 2001, pp. 3229-3231, Vol. 78, No. 21.	
	AP	KASU, et al., "Field-emission characteristics and large current density of heavily Si-doped AlN and Al _x Ga _{1-x} N (0.38 ≤ x < 1)," Appl. Phys. Lett., November 26, 2001, pp. 3642-3644, Vol. 79, No. 22.	
	AQ	TONDARE, et al., "Field emission from open ended aluminum nitride nanotubes," Appl. Phys. Lett., June 24, 2002, pp. 4813-4815, Vol. 80, No. 25.	
TW	AR	SHE, et al., "Silicon tip arrays with ultrathin amorphous diamond apexes," Appl. Phys. Lett., November 25, 2002, pp. 4257-4259, Vol. 81, No. 22.	

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